



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

BC184, B, C TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.35 W ($T_{amb}=25^{\circ}C$)

Collector current

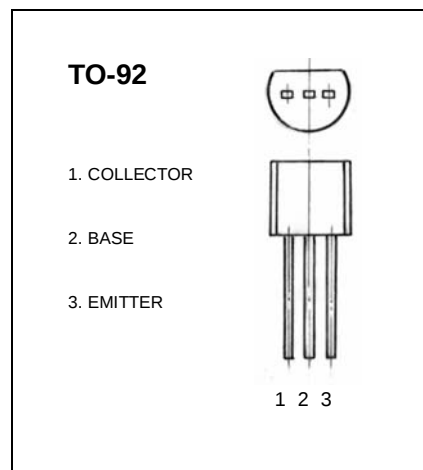
I_{CM} : 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: 45 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	45		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=2mA, I_B=0$	30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=30V, I_E=0$		15	nA
Collector cut-off current	I_{CEO}	$V_{CE}=30V, I_B=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$		15	nA
DC current gain BC184 BC184B BC184C	$h_{FE(1)}$	$V_{CE}=5V, I_C=2mA$	240 240 450	900 500 900	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=5mA$		0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=5mA$		1.2	V
Transition frequency	f_T	$V_{CE}=5V, I_C=10mA$ $f=100MHz$	150		MHz